### **BS170**

# Small Signal MOSFET 500 mA, 60 Volts

**N-Channel TO-92 (TO-226)** 

#### **Features**

• This is a Pb-Free Device\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	Vdc
Gate-Source Voltage - Continuous - Non-repetitive (t <sub>p</sub> ≤ 50 μs)	V <sub>GS</sub> V <sub>GSM</sub>	±20 ±40	Vdc Vpk
Drain Current (Note)	I <sub>D</sub>	0.5	Adc
Total Device Dissipation @ T <sub>A</sub> = 25°C	P <sub>D</sub>	350	mW
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: The Power Dissipation of the package may result in a lower continuous drain current.

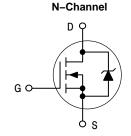
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



#### ON Semiconductor®

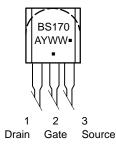
www.onsemi.com

## 500 mA, 60 Volts $R_{DS(on)} = 5.0 \Omega$





### MARKING DIAGRAM & PIN ASSIGNMENT



A = Assembly Location

Y = Year
WW = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### **BS170**

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Gate Reverse Current $(V_{GS} = 15 \text{ Vdc}, V_{DS} = 0)$	I <sub>GSS</sub>	-	0.01	10	nAdc
Drain-Source Breakdown Voltage $(V_{GS} = 0, I_D = 100 \mu Adc)$	V <sub>(BR)DSS</sub>	60	90	-	Vdc
ON CHARACTERISTICS (Note 1)				•	
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$	V <sub>GS(Th)</sub>	0.8	2.0	3.0	Vdc
Static Drain–Source On Resistance (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 200 mAdc)	r <sub>DS(on)</sub>	-	1.8	5.0	Ω
Drain Cutoff Current (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0 Vdc)	I <sub>D(off)</sub>	-	-	0.5	μΑ
Forward Transconductance (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 250 mAdc)	9fs	-	200	-	mmhos
SMALL-SIGNAL CHARACTERISTICS					
Input Capacitance (V <sub>DS</sub> = 10 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>iss</sub>	-	-	60	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (I <sub>D</sub> = 0.2 Adc) See Figure 1	t <sub>on</sub>	-	4.0	10	ns
Turn-Off Time (I <sub>D</sub> = 0.2 Adc) See Figure 1	t <sub>off</sub>	-	4.0	10	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BS170	TO-92 (TO-226) (Pb-Free)	1000 Unit/Tube
BS170RLRAG	TO-92 (TO-226) (Pb-Free)	2000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

#### **BS170**

#### **RESISTIVE SWITCHING**

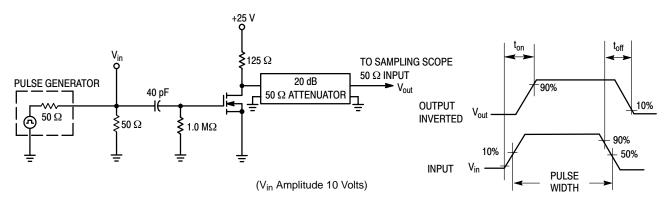


Figure 1. Switching Test Circuit

Figure 2. Switching Waveforms

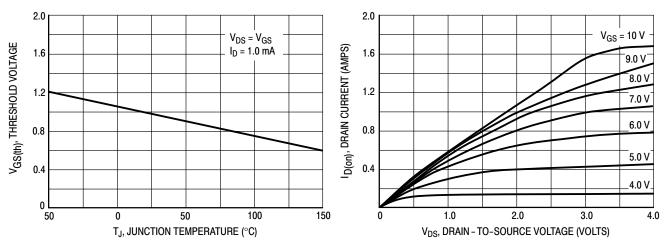


Figure 3. V<sub>GS(th)</sub> Normalized versus Temperature

Figure 4. On-Region Characteristics

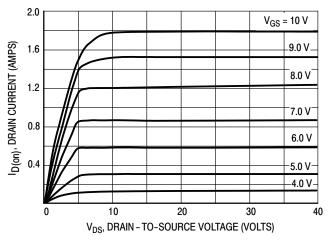


Figure 5. Output Characteristics

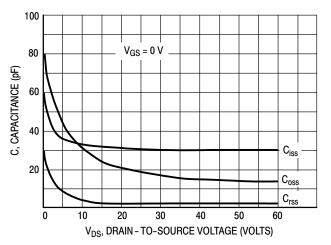
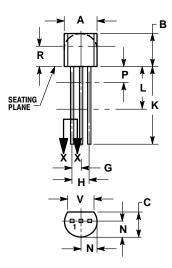


Figure 6. Capacitance versus Drain-To-Source Voltage

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM

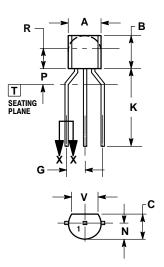


STRAIGHT LEAD **BULK PACK** 



- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
  IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



**BENT LEAD** TAPE & REEL AMMO PACK



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

- ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  CONTOUR OF PACKAGE BEYOND
  DIMENSION R IS UNCONTROLLED.
  LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MIN MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
Р	1.50	4.00	
R	2.93		
v	3 43		

STYLE 30: PIN 1. DRAIN 2. GATE 3.

SOURCE

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